## Promising submicron Nb and Al based Josephson junction for superconducting circuits

K.B. Polevoy<sup>1, 2,\*</sup>, S. V. Bakurskiy<sup>1,2,3</sup>, V. I. Ruzhickiy<sup>1,2,3</sup>, A. G. Shishkin<sup>1, 2</sup>, V. S. Stolyarov<sup>1, 2</sup>

<sup>1</sup> Moscow Institute of Physics and Technology,Russia

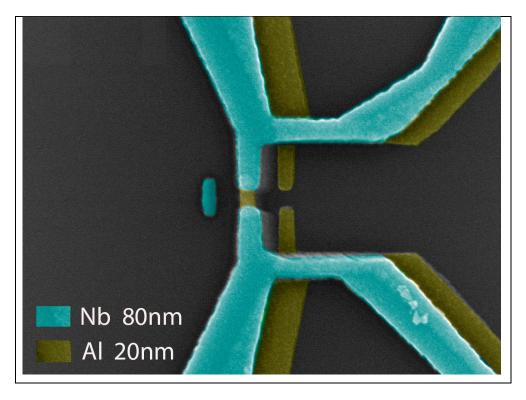
<sup>2</sup> All-Russian Research Institute of Automatics n.a. N.L. Dukhov (VNIIA), Russia

<sup>3</sup> Skobeltsyn Institute of Nuclear Physics, Lomonosov Moscow State University, Russia

\*email: polevoy.kb@phystech.edu

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In this report, we present results of fabrication and characterization of submicron planar Nb/Al Josephson junctions with an active area of  $5 \times 10^4$  nm². The study demonstrates that the use of aluminum as a weak link material significantly enhances the critical current across the entire temperature range due to the proximity effect. At a temperature of 4.2 K, the junction exhibits non-hysteretic current-voltage characteristics, making it a promising candidate for superconducting digital electronics. The device shows characteristic voltages up to 7 mV and critical currents around 50  $\mu$ A.



Pic.1 SEM image of one of studied junctions. Al layer painted as green, Nb layer painted as blue.